



# NANOWAVE Technologies Inc.

## SSPA for Pulsed Operation

Version 1.6



Date: Jun 1, 2015

## CONTENT

<b>Product Overview</b> .....	<b>3</b>
<b>FACTS ON THE TECHNOLOGY</b> .....	<b>4</b>
<b>SOLID-STATE POWER AMPLIFIERS</b> .....	<b>5</b>
<b>ABOUT NANOWAVE</b> .....	<b>9</b>

## RF Components and Subsystems

NANOWAVE Technologies Inc. is a privately owned Canadian manufacturer of advanced high reliability RF and microwave components, modules and subsystems for the Aerospace, Avionics, Defense, Industrial and Medical markets.

At NANOWAVE all critical processes are conducted in-house to provide a controlled supply chain to the end customer over product life spans up to and beyond 20 years. In house processes include:

- Packaging and Housing Technology
- Thin-Film Technology
- Semiconductor Device and MMIC Design
- RF Circuit Engineering
- RF Filter Design
- Circuit Card Design and Manufacturing
- Assembly and Integration
- Electrical and Environmental testing
- Quality Assurance

The foundation of the NANOWAVE product is a proprietary, high reliability, hybrid monolithic integrated circuit (HMIC) process. The HMIC process integrates bare die with in-house thin film circuits which are then hermetically sealed within a modular assembly. The resultant circuits can be sustained

over product lifetimes of up to and beyond 20 years without change in module function or physical form fit making NANOWAVE product ideally suited to the high reliability long duration product requirements of aerospace and defense applications.

The RF subassemblies comprise Solid-State Power amplifiers, Up-/Down-Converters, Filters, Synthesizers, Low-Noise Receivers, and Limiters. All RF blocks can be complemented by sophisticated Digital Control Interfaces, which allow interrogation from supervision systems, enabling remote status reporting on all major subsystem parameters, such as voltages, currents, or RF power levels.

NANOWAVE uses the following integrated circuit processes in its HMIC modules and is continuously reviewing and assessing the potential of new technologies to address customer requirements:

- Gallium Nitrid (GaN)
- Gallium Arsenid (GaAs)
- Silicon Germanium (SiGe)
- Bi-polar CMOS (BiCMOS)
- High Power Silicon (LDMOS)
- Indium Phosphide (InP)

# Product Overview

NANOWAVE's product portfolio covers a wide range of RF modules, components, subsystems, systems and sophisticated assemblies for the following Markets

- Commercial Aerospace
- Defense
- Communications
- Industrial
- Medical

NANOWAVE RF products can be found in applications such as

- Airborne and Ground-based RADAR
- SatCom
- Terrestrial Communication

NANOWAVE's Aerospace products can be found on the following platforms







Category Market	GaAs / GaN Die	Thin Film	Transmitter < 400 W	Transmitter > 400 W	Signal Sources	Frequency Converter	High-Power Transceiver	Broadband SSPA	Active Array
Commercial Aerospace (CA)	 GaAs/GaN FET & MMIC	 nF Capacitor	 100/200 W Gann			 Miniature Tx / Rx			
Defense		 Thick Copper substrate	 400 W X-Band Tx	 4 kW L-Band (Pulsed)	 L- to X-Band Synthesizer	 Data Link Tx/Rx		 6 to 18 GHz 1.5 W CW	
SatCom & Fiber Optics		 LASER Mount	 200 W INMARSAT Tx						 Ka-Band Array
Industrial		 5-pole SIW Filter		 600 W X-Band (Pulsed)	 C-Band STALO	 X-Band RADAR Test Set		 2-4 GHz 100W CW SSPA	
Medical		 Quartz Capacitor							

Fig. 1: Overview on NANOWAVE's Product Portfolio and Markets

# FACTS ON THE TECHNOLOGY

## ACTIVE DEVICE TECHNOLOGY

NANOWAVE uses GaN, GaAs, SiGe, BiCMOS, LDMOS, and InP bare die active devices in its RF subassemblies in order to obtain

- Best possible thermal management
- High efficiency
- Lowest parasitics
- Smallest size
- Multi-octave matching
- Multi-decade obsolescence mitigation

All RF subassemblies are packaged into hermetically sealed housings to achieve high reliability and high MTBF performance.

## KEY TECHNOLOGIES

NANOWAVE has all manufacturing technologies in-house to produce high volumes of complex assemblies. This comprises

- Engineering
- Chip Design
- Thin Film Technology
- Packaging Technologies (Machining, Reflow)
- Surface Mount Technology (PCB and Ceramic)

- Hybrid Module Assembly (Pick & Place, Eutectic Pick & Place, Automated Wire Bonding)
- Integration
- Test & Tune
- Quality Assurance (Electrical and Environmental testing)

## FREQUENCY BAND DEFINITION

Band	Frequency Range
L	1.0 - 2.0
S	2.0 - 4.0
C	4.0 - 8.0
X	8.0 - 12.0
Ku	12.0 - 18.0
Ka	28.0 - 32.0
BB	Broad band (multi octave)

## QUALITY ASSURANCE

NANOWAVE Technologies Inc. is certified to the following standards

- ISO 9001:2008
- AS 9100

The products are qualified and tested according to the following standards:

- DO-160
- MIL-STD-883
- MIL-C-9858A
- MIL-PRF-38534C



## SOLID-STATE POWER AMPLIFIERS

The SSPAs comprise a building block architecture based on bare die power devices from various technologies including:

- Gallium Nitride (GaN)
- Gallium Arsenide (GaAs)
- Silicon Germanium (SiGe)
- High Power Silicon (LDMOS)
- Indium Phosphide (InP)

Utilizing bare-die devices in all RF sections, NANOWAVE has full control on thermal and RF characteristics for pulsed and CW operated small-band or broad band circuits. Power amplifier designs range from fast, pulsed to CW operated with very high linearity in both, amplitude and phase behaviour.

### SSPA MODULES FOR PULSED OPERATION

NANOWAVE provides a series of SSPA power bricks covering the frequency range from 1 GHz (L-band) to 36 GHz (Ka-band) and output power levels from 10 W to 200 W per module. These power bricks form a

*Building Block* system that enables scaling up of combined output power levels into the kW regime utilizing NANOWAVE's low-loss power combiners.

#### Application:

- Weather Radar
- Airborne or Ground-based Radar
- Surveillance Radar
- Reconnaissance Radar

#### Special Features:

- Arbitrary load capability
- High efficiency GaN (or GaAs)
- High pulse-to-pulse stability
- Low pulse droop
- Large range of pulse width and duty cycle options
- Integrated Modulator and charge capacitor bank
- Integrated Digital Control Functionality (optional)
- Single Supply Voltage (optional)
- Low Rise / Fall Times of < 100 ns
- Digital control interface (I2C, RS232, TCP/IP)
- Operating temperature range -50 °C to +95°C (depending on model and requirement)



Fig. 2: 1 kW L-Band SSPA Module

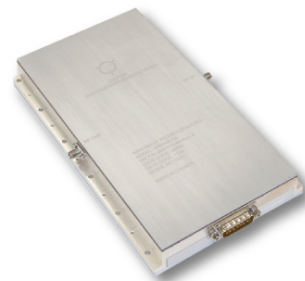


Fig 3: Hermetically sealed X-Band SSPA Power brick (individual modules may vary in shape and size)

### Selection Guide for Pulsed SSPA Modules

Model Number	Band	Frequency GHz	Pout dBm 1)	Gain dB	Ripple dB	PW max us	DC max %	Operating Temperature °C	Vd V	Id A	Size inch
NW103110-60	L	1.03 - 1.06	60.0 1)	15	±0.15	34	2	-25 - +65	34	1.4	9.0 x 5.2 x 1.1
NW2729-56	S	2.7 - 2.9	56.0 1)	29	±1.0	100	12	+10 - +40	32 2)	5 2)	9.3 x 5.0 x 1.0
NW8996-50	X	8.9 - 9.6	50.0	29	±0.35	55	15	-10 - +65	10 2)	9	8.3 x 4.8 x 0.85
NW8996-50-1	X	8.9 - 9.6	50.5	29	±0.25	50	15	-5 - +60	34 2)	1.7	6.9 x 5.1 x 0.81
NWPAG9092-49	X	9.0 - 9.2	50.8	42	±0.25	4	8	-40 - +70	34 2)		6.12 x 3.98 x .93
NW1517-50	Ku	15.5 - 17.5	50.0 1)	29	±0.15	200	40	-30 - +85	34 2)	1 2)	8.3 x 4.8 x 0.85

**Notes:**

- 1) Saturated output power (≥ 3 dB saturation)
- 2) Multi supply voltages required (see Data Sheet for details)

All specifications are subject to change without notice.

Full Data Sheets of NANOWAVE products are available on request at [sales@Nanowavetech.com](mailto:sales@Nanowavetech.com).

## SSPA UNITS FOR PULSED OPERATION

NANOWAVE provides a series of Solid-State Power Amplifier Transmitter units in 19" rack mountable chassis or custom designed housings based on the SSPA power bricks.

The total output power ranges from several 100 W to 10 kW (higher output power possible on request), covering the frequency range from L- to Ka-Band.

### Application:

- Weather Radar
- Airborne or Ground-based Radar
- IFF
- Surveillance Radar (e.g. ASR-S)
- Reconnaissance Radar



**Fig 4: 19" Rack Mountable C-Band Transmitter Unit**

### Special Features:

- Arbitrary load capability
- High efficiency
- High pulse-to-pulse stability
- Low pulse droop
- Large range of pulse width and duty cycle options
- Phase aligned for efficient combining of several units to kW range Transmitter systems
- Digital Control via Ethernet or other interface (proprietary, RS232, I2C, MODBUS, CAN)
- Web Browser based GUI (optional)
- AC supply voltage 110 to 240 V



**Fig 5: 19" Rack Mountable X-Band Transmitter Unit  
(Individual systems may vary in size, weight, front and back panel configuration)**

COMMERCIAL PRODUCTS

**Selection Guide for Transmitter Units**

Model Number	Band	Frequency GHz	Pout dBm	Gain dB	Ripple dB	PW max us	DC max %	Operating Temperature °C	Vd V	Id A	Size inch
NW103110-65-3	L	1.03 - 1.06	65.0	55	±0.15	34	2	-25 - +65	34	6.5	9.0 x 7.2 x 5.4
NW2729-62	S	2.7 - 2.9	62.0 1)	50	±0.5	100	12	+10 - +40	110/230	5 2)	19.0 x 4HU x 27.2
NW2729-70	S	2.7 - 2.9	70.0 1)	50	±0.5	100	12	+10 - +40	110/230	39 2)	19.0 x 42HU x 27.2
NW5457-54	C	5.4 - 5.7	54.0	54	±0.5	80	3	0	110/230	1.4 3)	19.0 x 4HU x 26.0
NW8995-55	X	8.9 - 9.6	55.0 1)	45	±0.5	55	16.5	+5 - +40	110/230	5.6 2)	19.0 x 2HU x 19.5
NW8996-57	X	8.9 - 9.6	57.0 1)	35	±0.4	50	15	-5 - +60	34 2)	14	6.9 x 5.1 x 0.81
NW105109-56	X	10.5 - 10.9	56.0 1)	36		15	25	-40 - +80	30 - 60		11.0 x 5.5 x 3.3
NW1517-52	Ku	15.5 - 17.5	52.0 1)	38	±0.15	200	40	-30 - +85	110/230	1.5 2)	13.8 x 11.8 x 7.9

**Notes:**

- 1) Saturated output power (≥ 3 dB saturation)
- 2) @ 230 V AC supply voltage
- 3) @ 110 V AC supply voltage
- 4) Over any 15 MHz band

All specifications are subject to change without notice.

Full Data Sheets of NANOWAVE products are available on request at [sales@nanowavetech.com](mailto:sales@nanowavetech.com).



## ABOUT NANOWAVE

---

NANOWAVE Technologies Inc. was founded in 1992 and is a leading Canadian Designer and Manufacturer of Advanced Microwave and Millimeter Wave Components and Sub-Systems for the Radar, Communications, Industrial and Medical markets.

The company's products can be found on the most advanced commercial and defense aircrafts, as well as ground based Radar and Communication Systems.

NANOWAVE's commitment to annual investments in R&D combined with in-house control of critical design, manufacturing and test processes results in rapid response to our customers' demands for:

- Customization
- Obsolescence Mitigation
- Demanding Technical Specifications
- On-time Delivery
- High Reliability
- Traceability



### **NANOWAVE Technologies Inc.**

425 Horner Avenue  
Etobicoke, Ontario M8W 4W3  
Canada

Phone: +1-416-252-5602  
Fax: +1-416-252-7077  
Email: [sales@nanowavetech.com](mailto:sales@nanowavetech.com)  
WWW: [www.nanowavetech.com](http://www.nanowavetech.com)

